



2SB1132

PNP SILICON TRANSISTOR

MEDIUM POWER TRANSISTOR

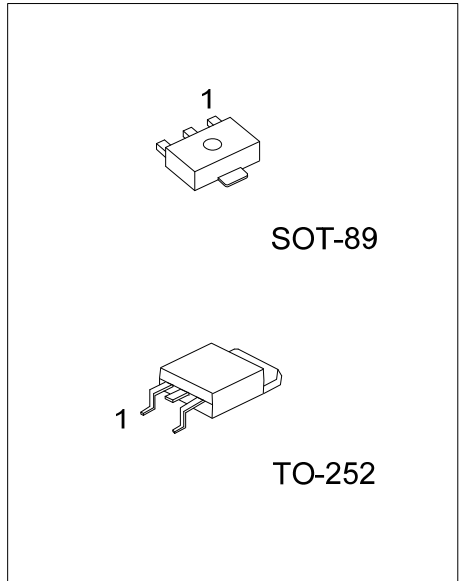
DESCRIPTION

The UTC **2SB1132** is a epitaxial planar type PNP silicon transistor.

FEATURES

* Low $V_{CE(SAT)}$.

$V_{CE(SAT)} = -0.2V(Typ.)$ ($I_C/I_B = -500mA/-50mA$)



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SB1132L-x-AB3-R	2SB1132G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB1132L-x-TN3-R	2SB1132G-x-TN3-R	TO-252	B	C	E	Tape Reel
2SB1132L-x-TN3-T	2SB1132G-x-TN3-T	TO-252	B	C	E	Tube

<p>2SB1132L-x-AB3-R</p> <p>(1)Packing Type (2)Package Type (3)Rank (4)Lead Free</p>	<p>(1) R: Tape Reel, T: Tube (2) AB3: SOT-89, TN3: TO-252 (3) x: refer to Classification of h_{FE} (4) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	DC	-1	A
Collector Current (Single pulse, Pw=100ms)	PULSE		
Collector Power Dissipation	SOT-89	0.5	W
	TO-252	1	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

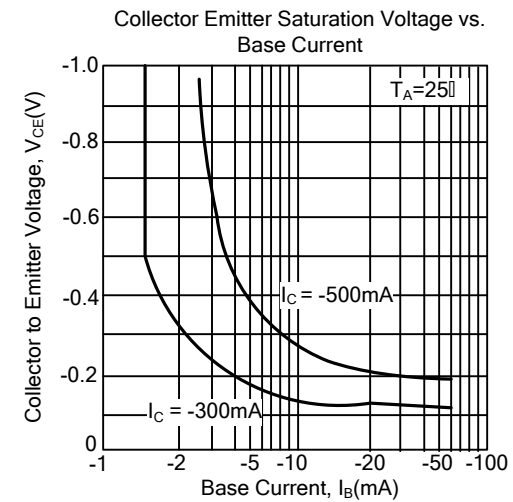
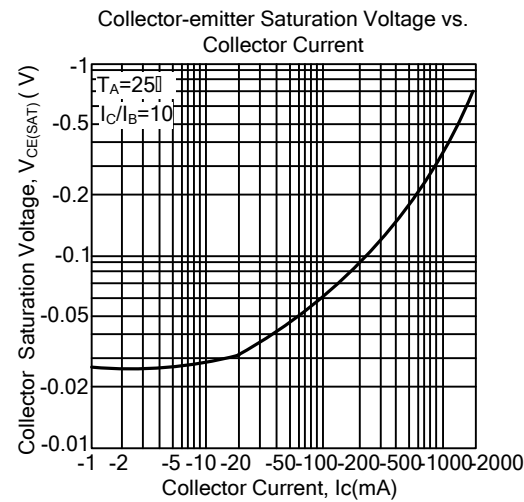
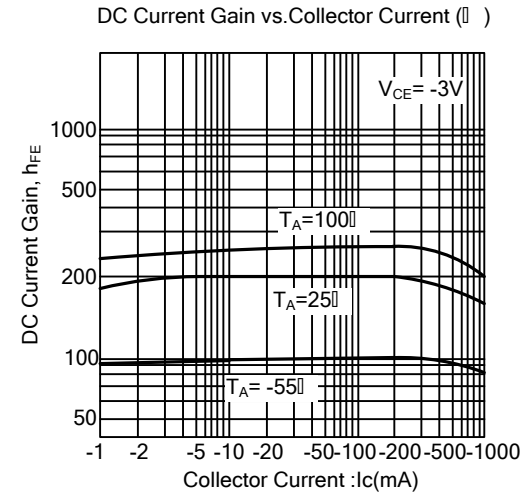
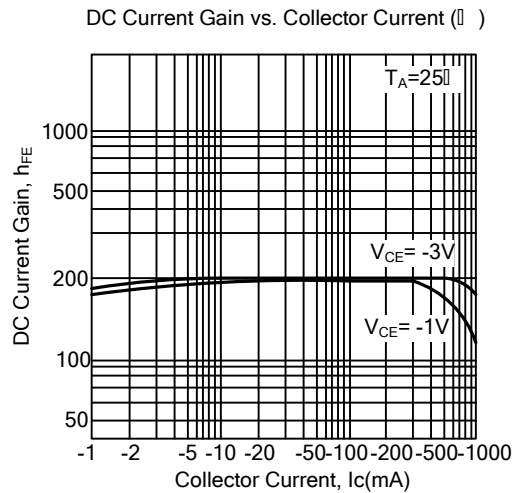
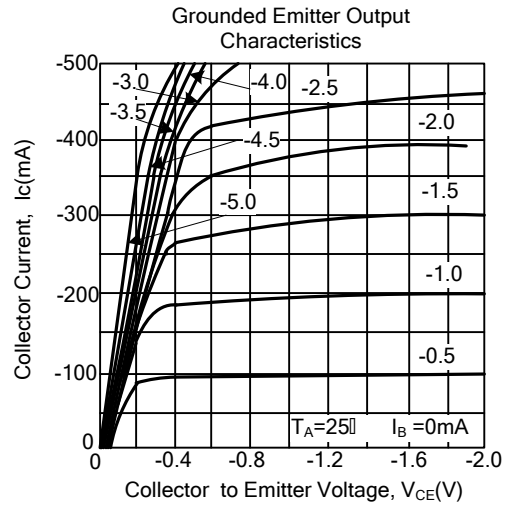
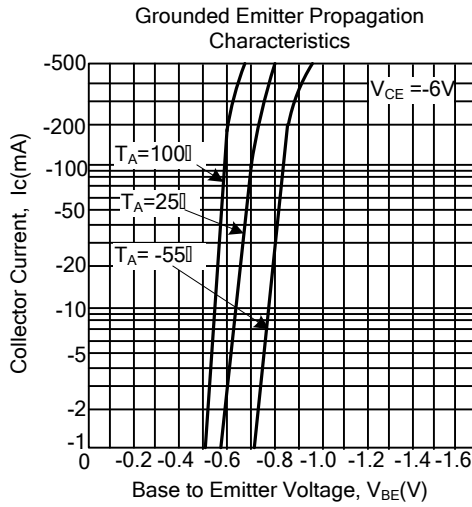
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV_{CBO}	$I_C = -50\mu\text{A}$	-40			V
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1\text{mA}$	-32			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E = -50\mu\text{A}$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -20\text{V}$			-0.5	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4\text{V}$			-0.5	μA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$ (Note)		-0.2	-0.5	V
DC Current Transfer Ratio	h_{FE}	$V_{CE} = -3\text{V}, I_C = -0.1\text{A}$ (Note)	82		390	
Transition Frequency	f_T	$V_{CE} = -5\text{V}, I_E = 50\text{mA}, f = 30\text{MHz}$		150		MHz
Output Capacitance	C_{OB}	$V_{CB} = -10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$		20	30	pF

Note: Measured using pulse current.

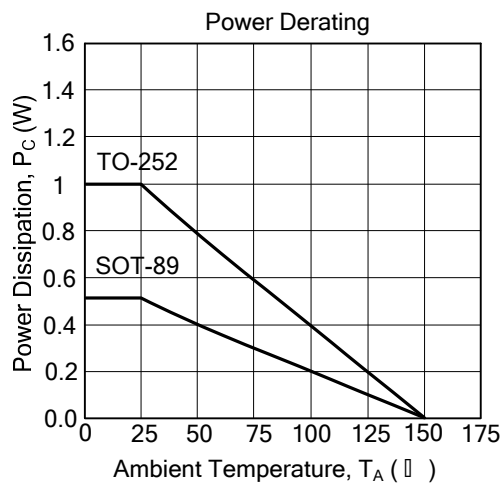
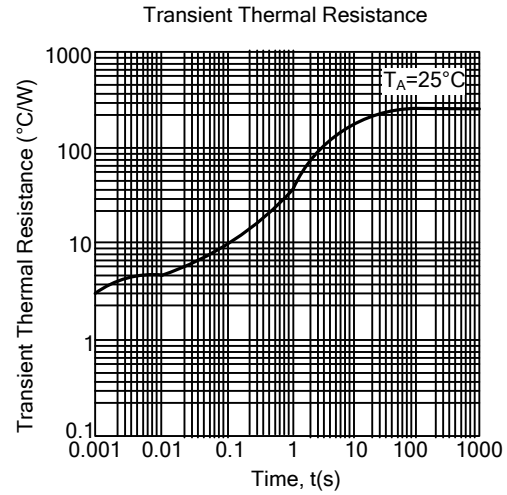
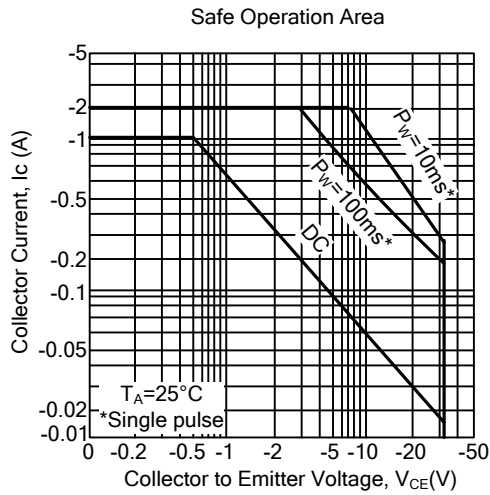
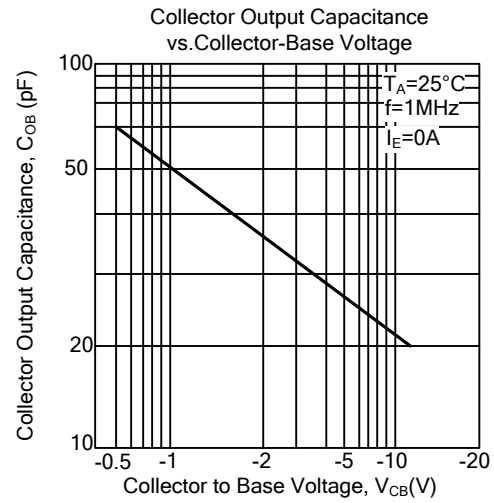
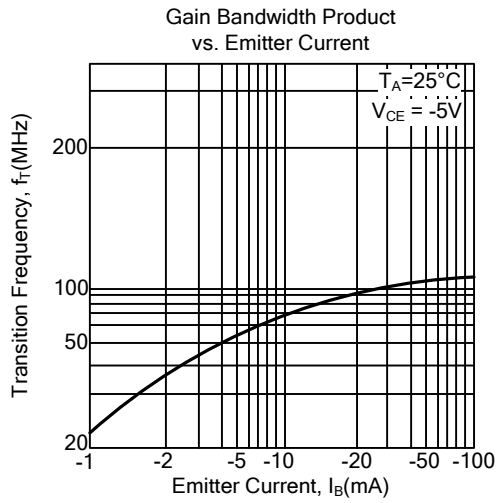
■ CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82-180	120-270	180-390

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS(Cont.)



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